

FEATURES

- Advanced trench process technology
- avalanche energy, 100% test
- Fully characterized avalanche voltage and current
- Lead free product

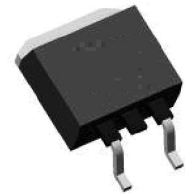
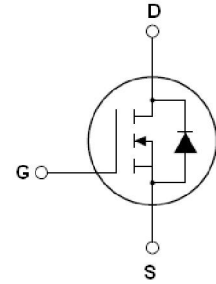
DESCRIPTION

The SSF6010A is a new generation of middle voltage and high current N-Channel enhancement mode trench power MOSFET. This new technology increases the device reliability and electrical parameter repeatability. SSF6010A is assembled in high reliability and qualified assembly house.

APPLICATIONS

- Power switching application

$I_D = 75A$
 $BV = 60V$
 $R_{DS(ON)} = 8m\Omega$ (typ.)



SSF6010A Top View (D2PAK)

Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D@T_c=25^\circ C$	Continuous drain current, $V_{GS}@10V$	75	A
$I_D@T_c=100^\circ C$	Continuous drain current, $V_{GS}@10V$	45	
I_{DM}	Pulsed drain current ①	300	
$P_D@T_c=25^\circ C$	Power dissipation	144	W
	Linear derating factor	0.74	W/°C
V_{GS}	Gate-to-Source voltage	± 20	V
E_{AS}	Single pulse avalanche energy ②	220	mJ
E_{AR}	Repetitive avalanche energy	TBD	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C

Thermal Resistance

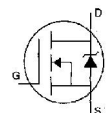
	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case	—	1.04	—	°C/W
$R_{\theta JA}$	Junction-to-ambient	—	—	62	

Electrical Characteristics @ $T_J=25^\circ C$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source breakdown voltage	60	—	—	V	$V_{GS}=0V, I_D=250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	8	10	m Ω	$V_{GS}=10V, I_D=30A$
$V_{GS(th)}$	Gate threshold voltage	2.0	—	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
g_{fs}	Forward transconductance	—	58	—	S	$V_{DS}=5V, I_D=30A$
I_{DSS}	Drain-to-Source leakage current	—	—	2	μA	$V_{DS}=60V, V_{GS}=0V$
		—	—	10		$V_{DS}=60V,$ $V_{GS}=0V, T_J=150^\circ C$
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS}=20V$
	Gate-to-Source reverse leakage	—	—	-100		$V_{GS}=-20V$

Q_g	Total gate charge	—	45	—	nC	$I_D=30A$ $V_{DD}=30V$ $V_{GS}=10V$
Q_{gs}	Gate-to-Source charge	—	4.2	—		
Q_{gd}	Gate-to-Drain("Miller") charge	—	15	—		
$t_{d(on)}$	Turn-on delay time	—	14.6	—	nS	$V_{DD}=30V$ $I_D=2A, R_L=15\Omega$ $R_G=2.5\Omega$ $V_{GS}=10V$
t_r	Rise time	—	14.2	—		
$t_{d(off)}$	Turn-Off delay time	—	40	—		
t_f	Fall time	—	7.3	—		
C_{iss}	Input capacitance	—	1480	—	pF	$V_{GS}=0V$ $V_{DS}=25V$ $f=1.0MHZ$
C_{oss}	Output capacitance	—	190	—		
C_{rss}	Reverse transfer capacitance	—	135	—		

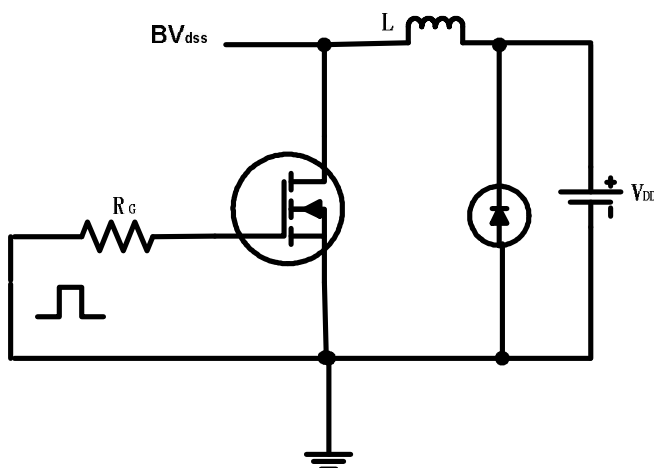
Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	75	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	300		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J=25^\circ C, I_S=40A, V_{GS}=0V$ ③
t_{rr}	Reverse Recovery Time	—	33	—	nS	$T_J=25^\circ C, I_F=60A$
Q_{rr}	Reverse Recovery Charge	—	61	—	nC	$di/dt=100A/\mu s$ ③
t_{on}	Forward Turn-on Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

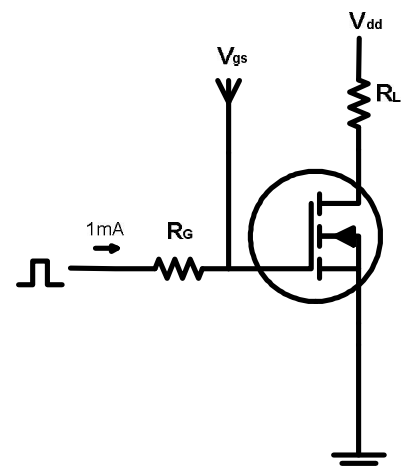
Notes:

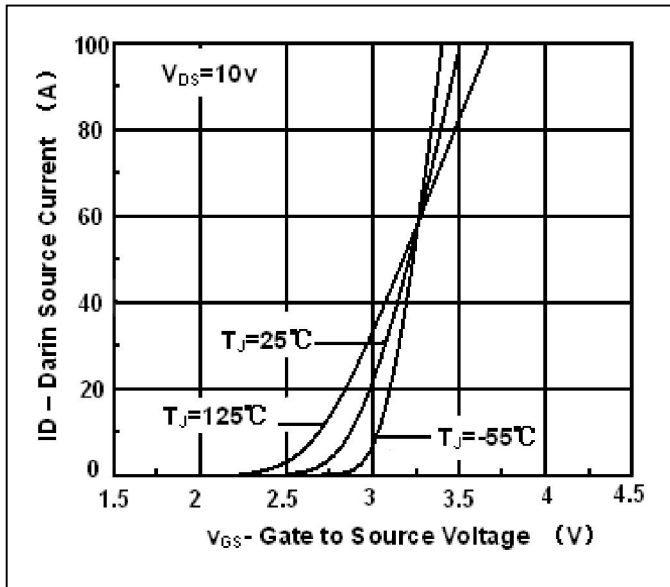
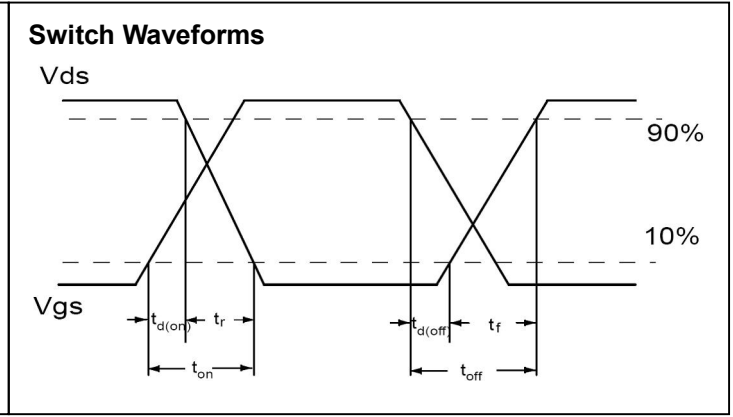
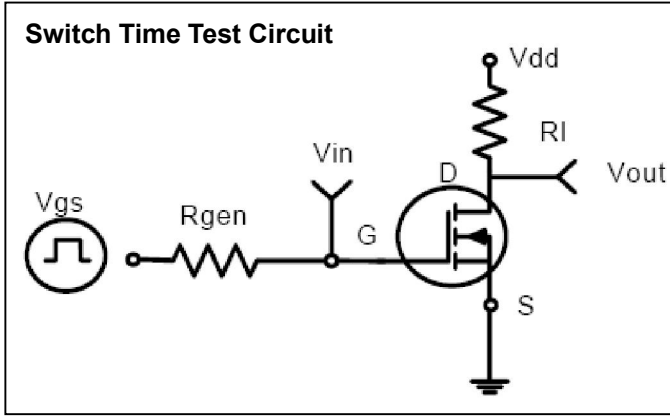
- ① Repetitive rating; pulse width limited by max junction temperature.
- ② Test condition: $L = 0.3mH, V_{DD} = 30V, I_D=37A$.
- ③ Pulse width $\leq 300\mu s$, duty cycle $\leq 1.5\%$; $R_G = 25\Omega$ Starting $T_J = 25^\circ C$.

EAS test circuit

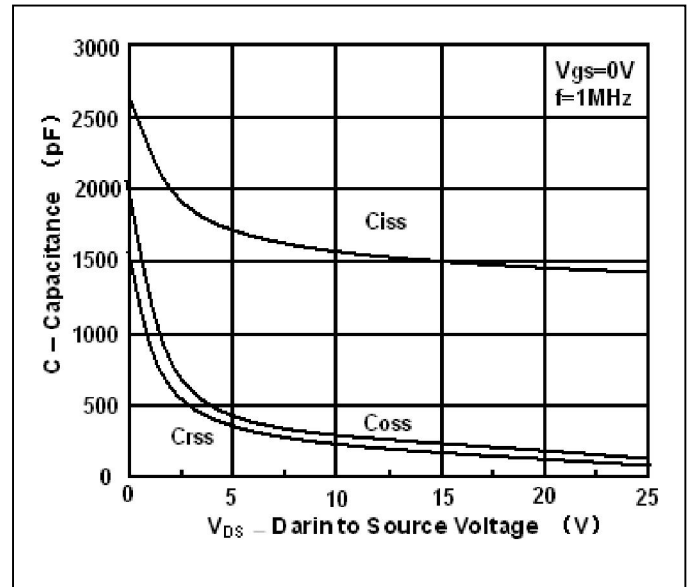


Gate charge test circuit

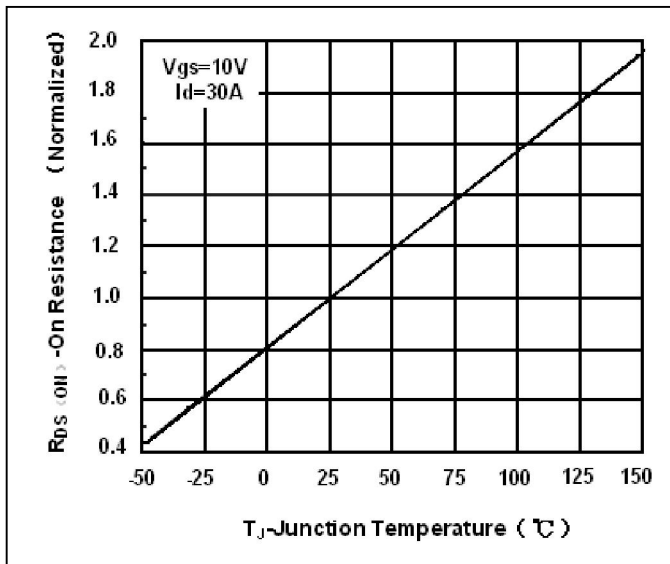




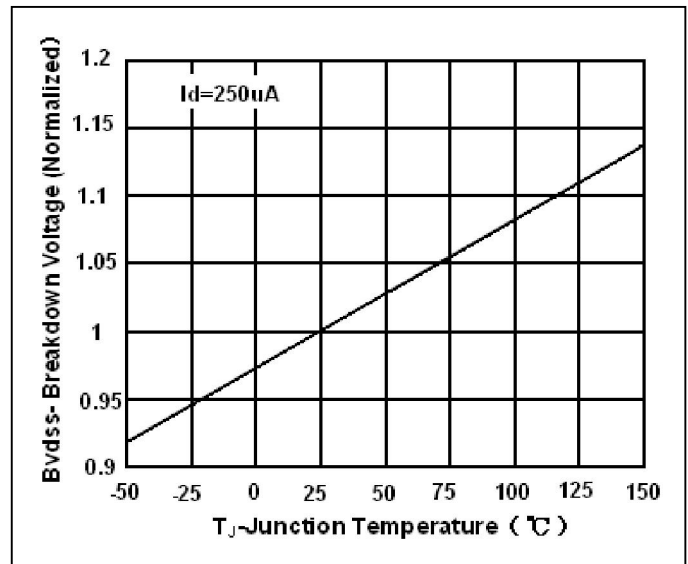
Transfer Characteristic



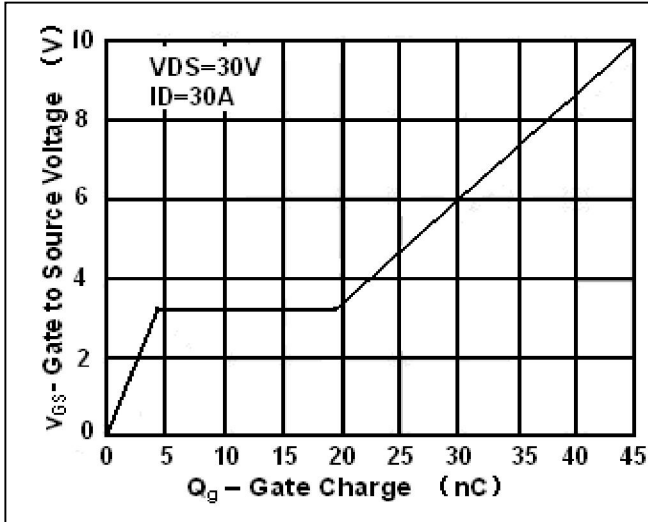
Capacitance



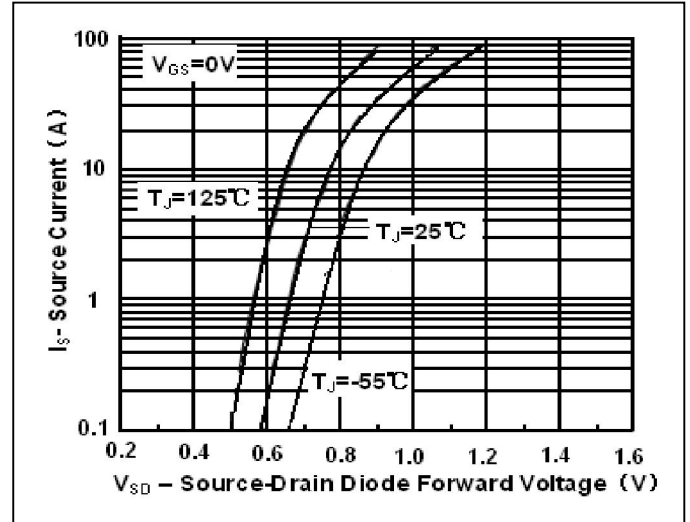
On Resistance vs. Junction Temperature



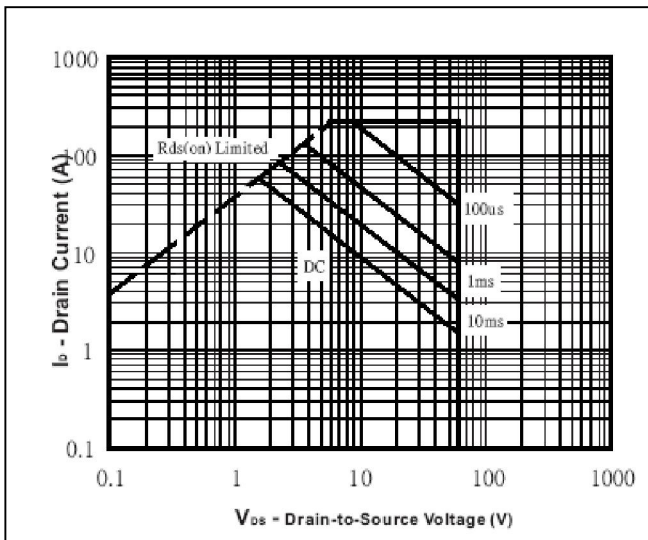
Breakdown Voltage vs. Junction Temperature



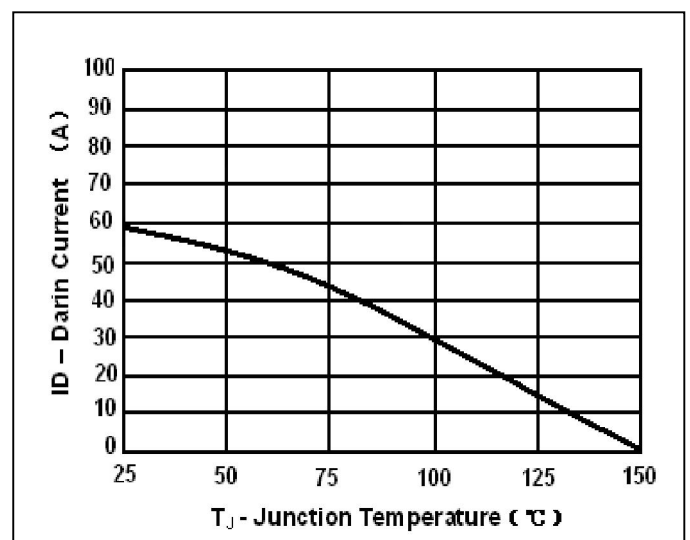
Gate Charge



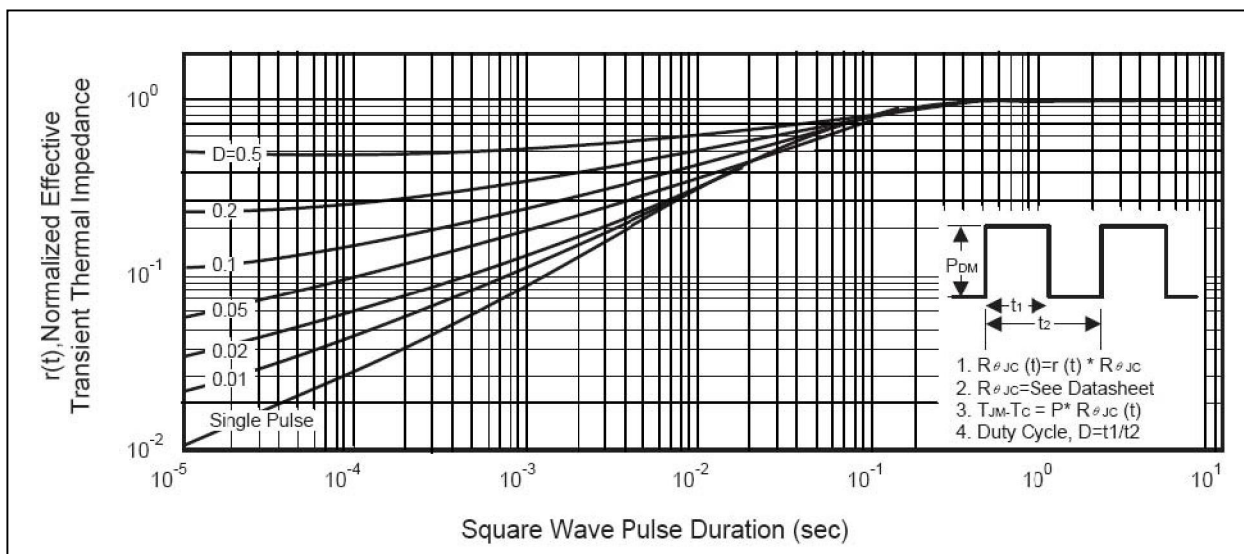
Source-Drain Diode Forward Voltage



Safe Operation Area



Max Drain Current vs. Junction Temperature



Transient Thermal Impedance Curve

TO263 (D2PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			

